AMENDMENTS TO THE CLAIMS

Claim 1 (previously presented) A method of forming a split programming virtual ground (SPVG) SONOS memory, comprising:

providing a substrate having at least a first conductive type well positioned in the substrate, and a plurality of select gate structures arranged in parallel and positioned on the first conductive type well;

forming a plurality of sacrificial spacers alongside each select gate structure;

performing an implantation process by utilizing the select gate structures and the sacrificial spacers as a mask to form a second conductive type doped region in the first conductive type well between two adjacent select gate structures;

removing the sacrificial spacers;

forming a composite dielectric layer covering the select gate structures subsequent to forming the second conductive type doped region in the first conductive type well between two adjacent select gate structures; and

forming a plurality of word lines perpendicular to the select gate structures on the composite dielectric layer.

Claim 2 (original) The method of claim 1, wherein each select gate structure from bottom to top comprises a gate insulating layer, a polysilicon layer, and a cap layer.

Claim 3 (original) The method of claim 1, wherein the second conductive type doped regions serve as buried bit lines.

Claim 4 (original) The method of claim 1, wherein the composite dielectric layer is an ONO tri-layer dielectric.

Claim 5 (original) The method of claim 1, wherein the first conductive type well is a P well.

Claim 6 (original) The method of claim 5, wherein each second conductive type doped region is an N doped region.

Claim 7 (previously presented) A method of forming a dual-bit storage nonvolatile memory, comprising:

providing a plurality of select gate structures arranged in parallel on the substrate;

forming a sacrificial spacer alongside each select gate structure;

performing an implantation process by utilizing the select gate structures and the sacrificial spacers as a mask to form a doped region in the substrate between any two adjacent select gate structures;

removing the sacrificial spacers;

forming a composite dielectric layer covering the select gate structures subsequent to forming the doped region in the substrate between any two adjacent select gate structures; and

forming a plurality of word lines perpendicular to the select gate structures on the composite dielectric layer.

Claim 8 (original) The method of claim 7, wherein each select gate structure from bottom to top comprises a gate insulating layer and a conductive layer.

Claim 9 (previously presented) The method of claim 8, wherein the conductive layer is a polysilicon layer, and the nonvolatile memory is a split programming virtual ground (SPVG) SONOS memory.

Claim 10 (previous presented) The method of claim 8, wherein the conductive layer is a metal layer, and the nonvolatile memory is a split programming virtual ground (SPVG) MONOS memory.

Claim 11 (original) The method of claim 7, wherein each select gate structure further comprises a cap layer positioned on the conductive layer.

Claim 12 (currently amended) The method of claim 7, wherein the substrate further comprises a ~~linear~~ liner oxide layer positioned on the substrate and covering each select gate structure.

Claim 13 (original) The method of claim 7, wherein the doped regions serve as buried bit lines.

Claim 14 (original) The method of claim 7, wherein the composite dielectric layer is an ONO tri-layer dielectric.

Claim 15 (original) The method of claim 7, wherein the substrate further comprises at least a well, and the select gate structures are positioned on the well.

Claim 16 (original) The method of claim 15, wherein the well is a P well, and each doped region is an N doped region.